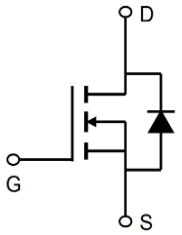
AP150N10NF

100V N-Channel Enhancement Mode MOSFET

Description

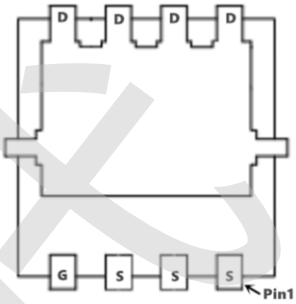
The AP150N10NF uses advanced **APM-SGT**ⅠⅠ technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.



General Features

V_{DS} = 100V I_D =150A

$R_{DS(ON)}$ < 4.5mΩ @ V_{GS}=10V **(Type：4.0mΩ)**



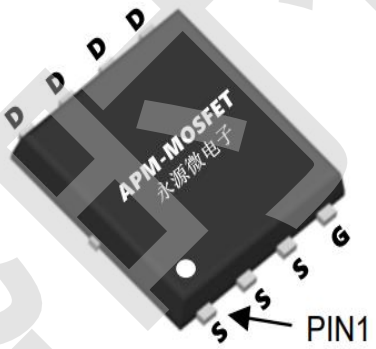
Application

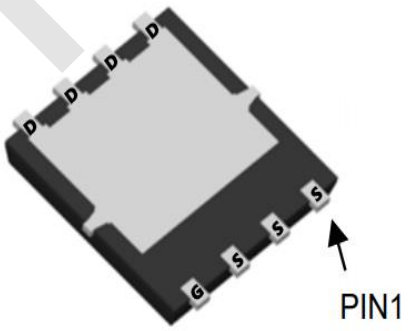
Isolated DC

Motor control

Synchronous-rectification

Clip packaging process





Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
AP120N10NF	PDFN5*6-8L	AP120N10NF XXX YYYY	5000

Absolute Maximum Ratings (T_C=25℃unless otherwise noted)

Symbol	Parameter	Rating	Units
VDS	Drain-Source Voltage	100	V
VGS	Gate-Source Voltage	±20	V
I_D@T_A=25℃	Continuous Drain Current[1]	150	A
I_D@T_A=70℃	Continuous Drain Current[1]	96	A
IDM	Pulsed Drain Current[2]	480	A
EAS	Single Pulse Avalanche Energy[3]	320	mJ
IAS	Avalanche Current	40	A
P_D@T_A=25℃	Total Power Dissipation[4]	131.6	W
TSTG	Storage Temperature Range	-55 to 150	℃
T_J	Operating Junction Temperature Range	-55 to 150	℃
$R_{\theta}JA$	Thermal Resistance Junction-Ambient [1]	25	℃/W
$R_{\theta}JC$	Thermal Resistance Junction-Case[1]	0.95	℃/W

电话:0755-83387360 手机：13826508770（王先生） 邮箱：3007605919@qq.com 网址：www.sztssd.com 地址:深圳市福田区中航路鼎诚国际南座18楼1814室

Electrical Characteristics (T_C=25℃unless otherwise noted)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V(BR)DSS	Drain-Source Breakdown Voltage	V_{GS} = 0V, I_D = 250μA	100	107	-	V
IGSS	Gate-body Leakage current	V_{DS} = 0V, V_{GS} = ±20V	-	-	±100	nA
IDSS	Zero Gate Voltage Drain Current T_J=25°C	V_{DS} =100V, V_{GS} = 0V	-	-	1	μA
	Zero Gate Voltage Drain Current T_J=100°C		-	-	100	
VGS(th)	Gate-Threshold Voltage	V_{DS} = V_{GS}, I_D = 250μA	2.0	3.0	4.0	V
RDS(on)	Drain-Source on-Resistance[4]	V_{GS} = 10V, I_D = 20A	-	4.1	4.5	mΩ
gfs	Forward Transconductance[4]	V_{DS} = 10V, I_D = 20A	-	62	-	S
Ciss	Input Capacitance	V_{DS} = 50V, V_{GS} =0V, f =1MHz	-	6865	-	pF
Coss	Output Capacitance		-	740	-	
Crss	Reverse Transfer Capacitance		-	21	-	
R_g	Gate Resistance	f =1MHz	-	1.3	-	Ω
Q_g	Total Gate Charge	V_{GS} = 10V, V_{DS} = 50V, I_D=20A	-	111.2	-	nC
Qgs	Gate-Source Charge		-	30.5	-	
Qgd	Gate-Drain Charge		-	27.3	-	
td(on)	Turn-on Delay Time	V_{GS} =10V, V_{DD} =50V, R_G = 3Ω, I_D= 20A	-	33	-	ns
t_r	Rise Time		-	39	-	
td(off)	Turn-off Delay Time		-	67.1	-	
t_f	Fall Time		-	32	-	
trr	Body Diode Reverse Recovery Time	I_F = 20A, dI/dt=100A/μs	-	58.7	-	ns
Q_{rr}	Body Diode Reverse Recovery Charge		-	97.3	-	nC
VSD	Diode Forward Voltage[4]	I_S = 20A, V_{GS} = 0V	-	-	1.2	V
IS	Continuous Source Current T_C=25°C	-	-	-	120	A

Note :

1、The data tested by surface mounted on a 1 inch 2 FR-4 board with 2OZ copper.

2、The data tested by pulsed , pulse width ≦ 300us , duty cycle ≦ 2%

3、The EAS data shows Max. rating . The test condition is VDD=72V,VGS=10V, L=0.1mH IAS=40A

4、The power dissipation is limited by 150℃ junction temperature

5、The data is theoretically the same as I D and I DM , in real applications , should be limited by total power dissipation

电话:0755-83387360 手机：13826508770（王先生） 邮箱：3007605919@qq.com 网址：www.sztssd.com 地址:深圳市福田区中航路鼎诚国际南座18楼1814室

Typical Characteristics

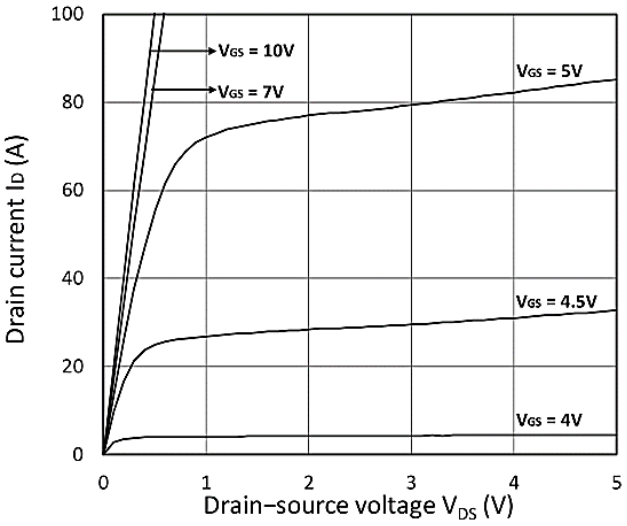


Figure 1. Output Characteristics

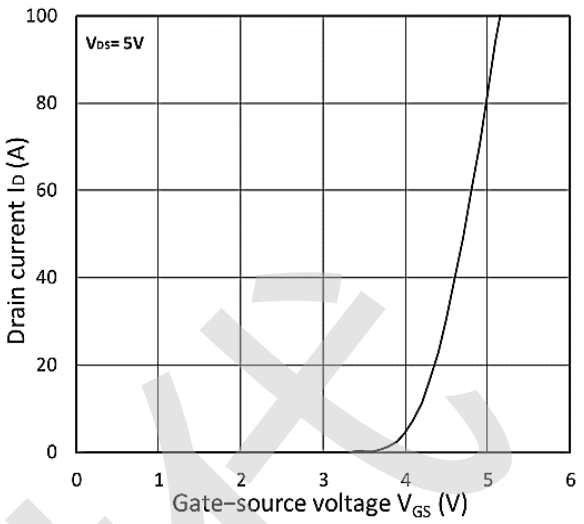


Figure 2. Transfer Characteristics

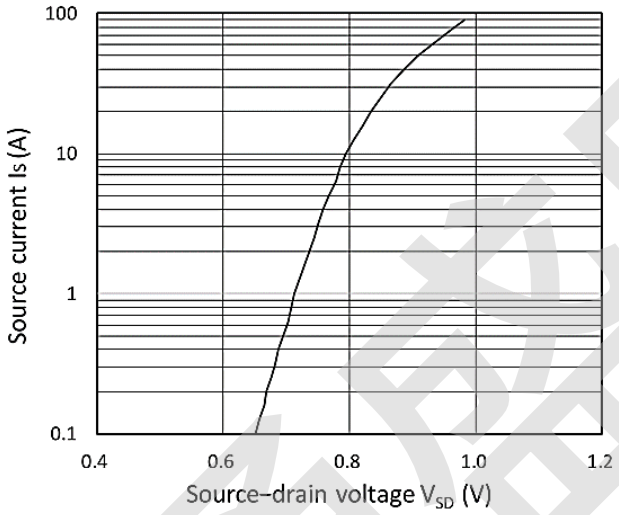


Figure 3. Forward Characteristics of Reverse

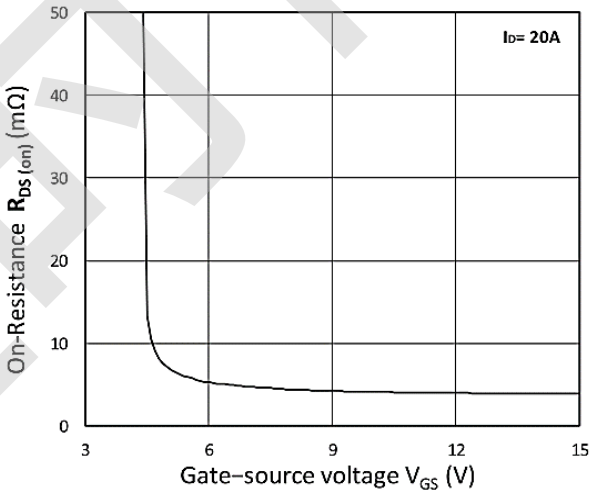


Figure 4. RDS(ON) vs. VGS

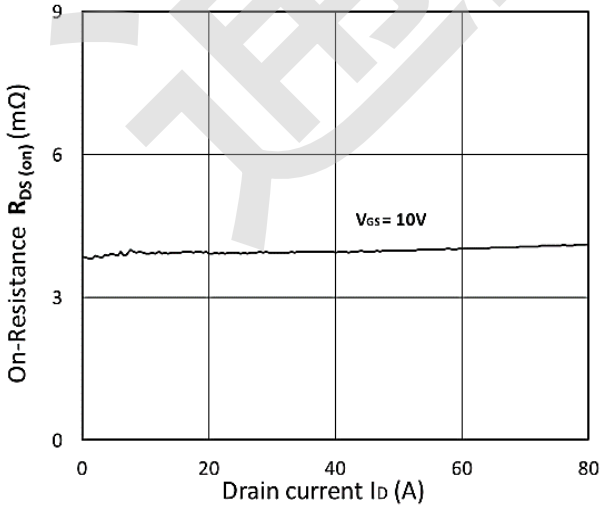


Figure 5. RDS(ON) vs. ID

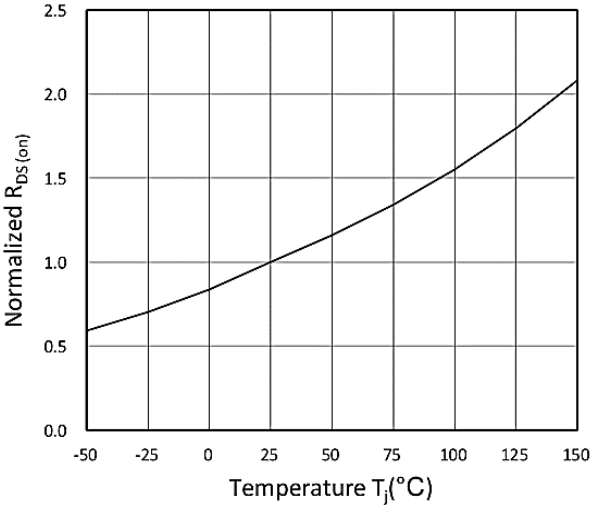


Figure 6. Normalized RDS(on) vs. Temperature

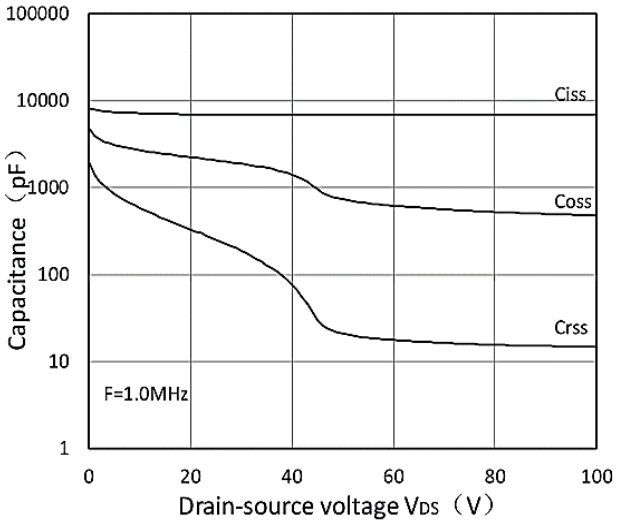


Figure 7. Capacitance Characteristics

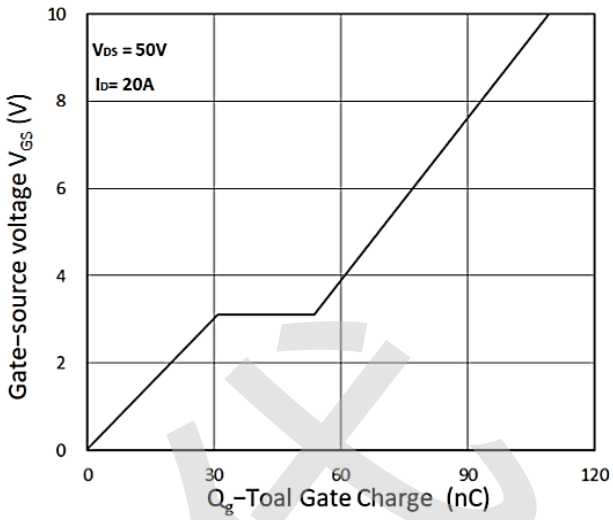


Figure 8. Gate Charge Characteristics

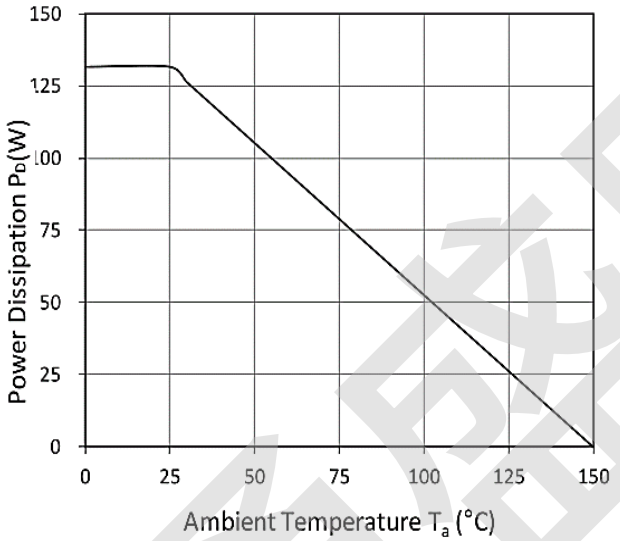


Figure 9. Power Dissipation

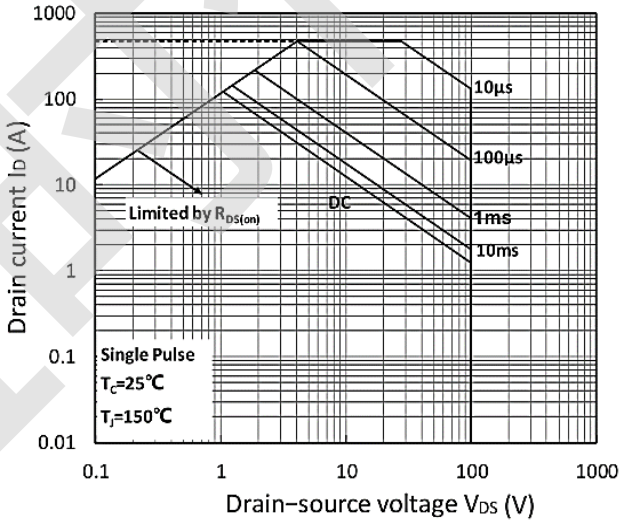


Figure10. Safe Operating Area

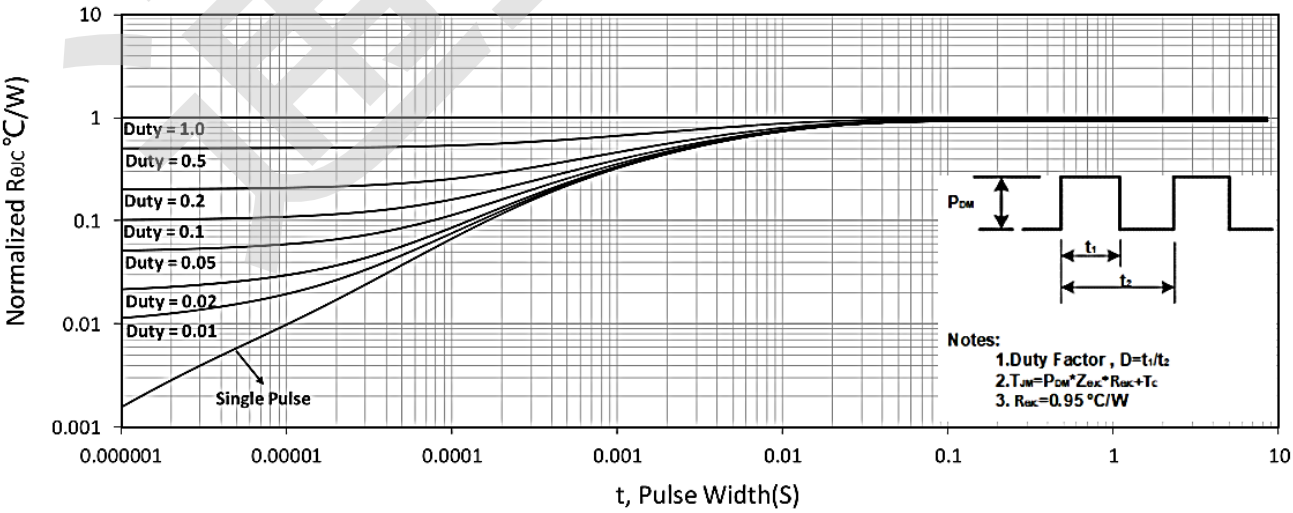
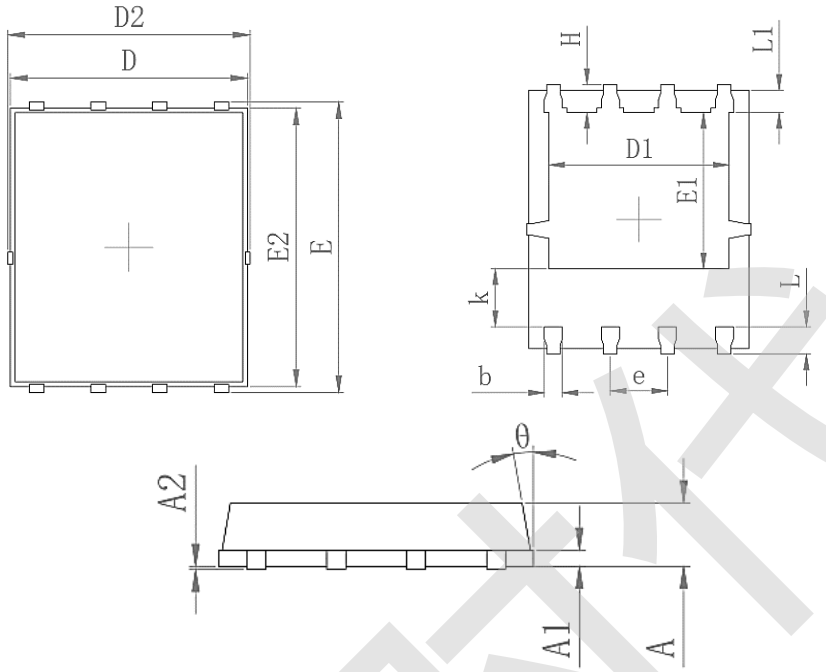


Figure 11. Normalized Maximum Transient Thermal Impedance

电话:0755-83387360 手机：13826508770（王先生） 邮箱：3007605919@qq.com 网址：www.sztssd.com 地址:深圳市福田区中航路鼎诚国际南座18楼1814室

Package Mechanical Data-PDFN5X6-8L-XZT Single



Symbol	Common	
	mm	
	Mim	Max
A	0.90	1.10
A1	0.254 REF	
A2	0-0.05	
D	4.824	4.976
D1	3.910	4.110
D2	4.944	5.076
E	5.924	6.076
E1	3.375	3.575
E2	5.674	5.826
b	0.350	0.450
e	1.270	
L	0.534	0.686
L1	0.424	0.576
K	1.190	1.390
H	0.549	0.701
Φ	8°	12°

电话:0755-83387360 手机：13826508770（王先生） 邮箱: 3007605919@qq.com 网址：www.sztssd.com 地址:深圳市福田区中航路鼎诚国际南座18楼1814室

Attention

1,Any and all APM Microelectronics products described or contained herein do not have specifications that can handle applications that require extremely high levels of reliability, such as life support systems, aircraft's control systems, or other applications whose failure can be reasonably expected to result in serious physical and/or material damage. Consult with your APM Microelectronics representative nearest you before using any APM Microelectronics products described or contained herein in such applications.

2,APM Microelectronics assumes no responsibility for equipment failures that result from using products at values that exceed, even momentarily, rated values (such as maximum ratings, operating condition ranges, or other parameters) listed in products specifications of any and all APM Microelectronics products described or contained herein.

3, Specifications of any and all APM Microelectronics products described or contained here instipulate the performance, characteristics, and functions of the described products in the independent state, and are not guarantees of the performance, characteristics, and functions of the described products as mounted in the customer's products or equipment. To verify symptoms and states that cannot be evaluated in an independent device, the customer should always evaluate and test devices mounted in the customer's products or equipment.

4, APM Microelectronics Semiconductor CO., LTD. strives to supply high quality high reliability products. However, any and all semiconductor products fail with some probability. It is possible that these probabilistic failures could give rise to accidents or events that could endanger human lives that could give rise to smoke or fire, or that could cause damage to other property. When designing equipment, adopt safety measures so that these kinds of accidents or events cannot occur. Such measures include but are not limited to protective circuits and error prevention circuits for safe design, redundant design,and structural design.

5,In the event that any or all APM Microelectronics products(including technical data, services) described or contained herein are controlled under any of applicable local export control laws and regulations, such products must not be exported without obtaining the export license from the authorities concerned in accordance with the above law.

6, No part of this publication may be reproduced or transmitted in any form or by any means,electronic or mechanical, including photocopying and recording, or any information storage or retrieval system, or otherwise, without the prior written permission of APM Microelectronics Semiconductor CO., LTD.

7, Information (including circuit diagrams and circuit parameters) herein is for example only; it is not guaranteed for volume production. APM Microelectronics believes information herein is accurate and reliable, but no guarantees are made or implied regarding its use or any infringements of intellectual property rights or other rights of third parties.

8, Any and all information described or contained herein are subject to change without notice due to product/technology improvement,etc. When designing equipment, refer to the "Delivery Specification" for the APM Microelectronics product that you Intend to use.

AP150N10NF

100V N-Channel Enhancement Mode MOSFET

Edition	Date	Change
Rve1.0	2021/1/31	Initial release

电话:0755-83387360 手机：13826508770（王先生） 邮箱: 3007605919@qq.com 网址：www.sztssd.com 地址:深圳市福田区中航路鼎诚国际南座18楼1814室